

# BGA7P320

## Pre-Driver for Doherty Power Amplifier

### Features

- Operation frequency range: 3300 to 4200MHz
- Gain: 34.4dB
- Output P1dB: 27.8dBm
- 100 $\Omega$  differential input
- 3.3V supply voltage
- TSNP-16 leadless package (3.0 x 3.0 mm<sup>2</sup>)
- SiGe Technology

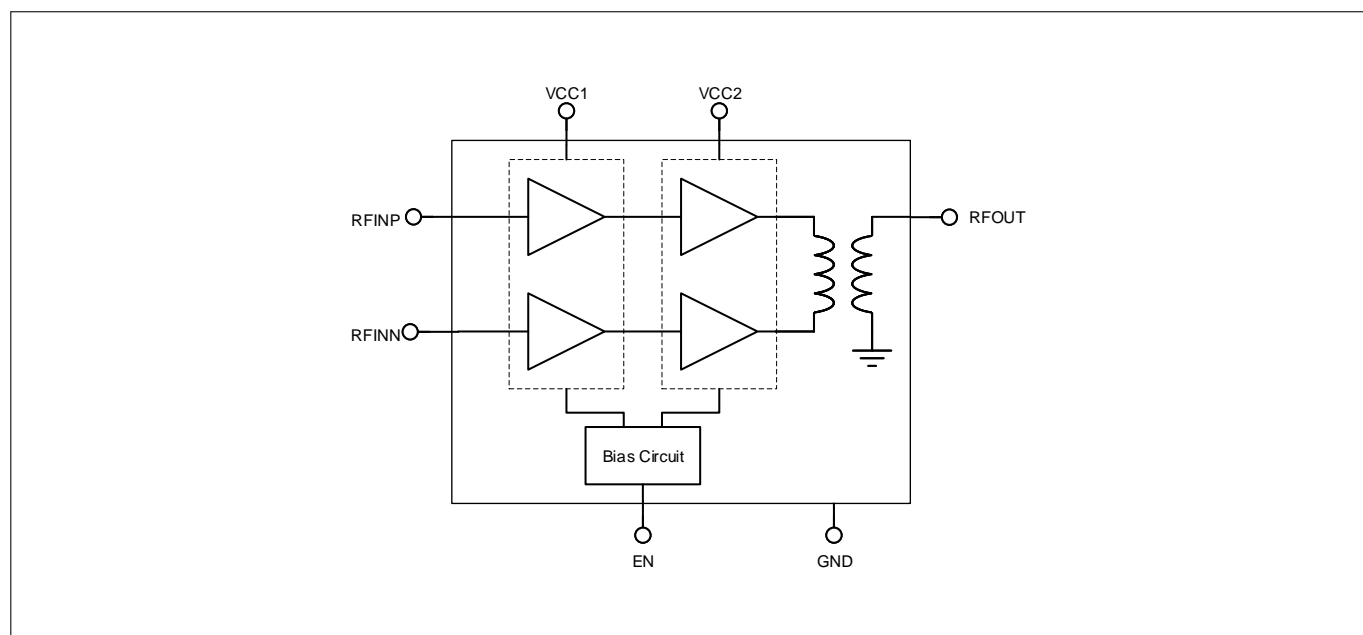
### Potential Application

- 5G m-MIMO
- Mobile Infrastructure

### Product Validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

### Block diagram



# BGA7P320

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### Table of Contents

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Table of Contents	1
1 Features	2
2 Maximum Ratings	3
3 Electrical Characteristics	4
4 Performance Variation	5
5 Application Information	6
6 Package Information	8

## Features

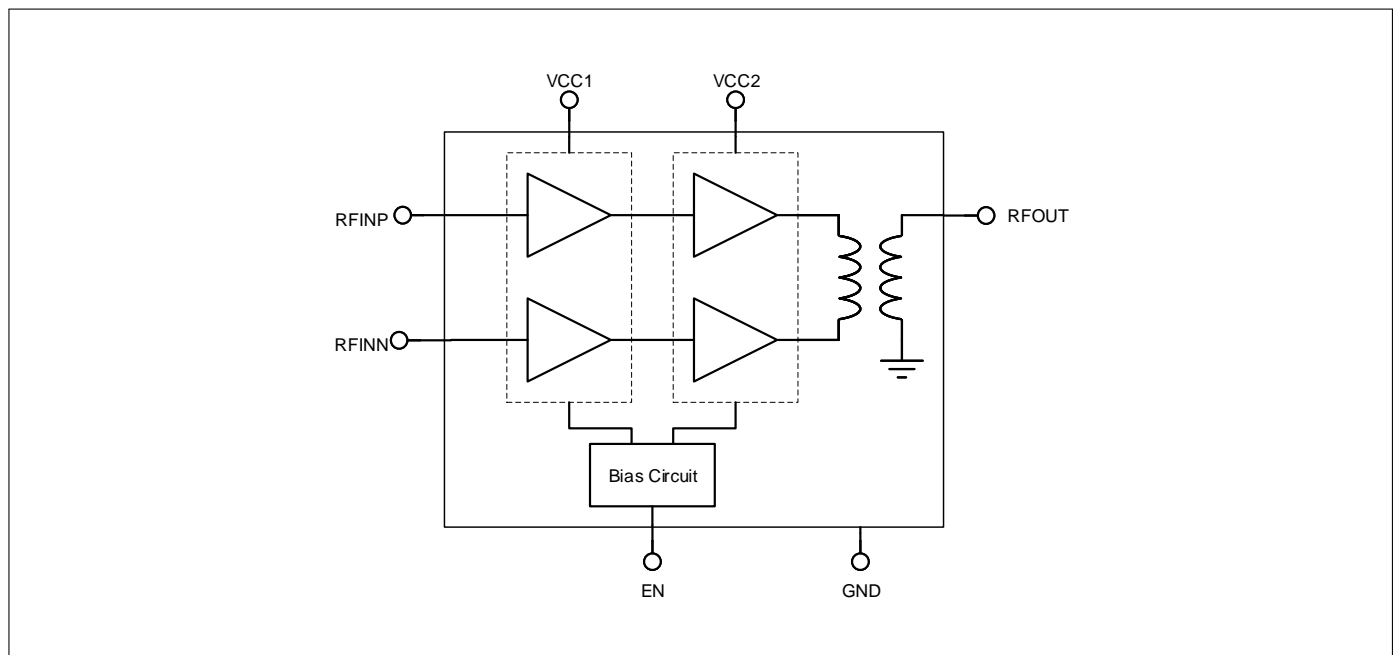
## 1 Features

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## Description

The product is a stand-alone pre-driver in package. The pre-driver is a two-stage amplifier designed to be used in the 5G Tx line-up for base station applications as the pre-driver for the Doherty power amplifier. It has been designed in the INFINEON SiGe technology. The input is 100 $\Omega$  differential, the output is 50 $\Omega$  single-ended.

The device configuration is shown in Fig. 1.



**Figure 1:** BGA7P320 Block diagram

Product Name	Marking	Package
BGA7P320	B7P320 YYWW(YY=year, WW=week)	PG-TSNP-16-12

**Maximum Ratings**

## 2 Maximum Ratings

**Table 1: Maximum Ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply Voltage	$V_{CC}$	-0.5	–	3.6	V	<sup>1</sup>
Storage Temperature	$T_{STG}$	-45	–	150	°C	–
Junction Temperature	$T_J$	-40	–	170	°C	–
DC voltage on RF Ports	$V_{RF,DC}$	0	–	0	V	<sup>1</sup>
RF Input Power CW	$P_{IN,CW}$	–	–	12	dBm	–
ESD Capability HBM <sup>2</sup>	$V_{ESD,HBM}$	–	–	2	kV	–
ESD Capability CDM <sup>3</sup>	$V_{ESD,CDM}$	–	–	500	V	–

<sup>1</sup>All voltages refer to GND-Nodes unless otherwise noted

<sup>2</sup>Human Body Model ANSI/ESDA/JEDECJS-001 (R = 1.5kΩ, C = 100pF)

<sup>3</sup>Field-Induced Charged-Device Model ANSI/ESDA/JEDECJS-002. Simulates charging/discharging events that occur in production equipment and processes. Potential for CDM ESD events occurs whenever there is metal-to-metal contact in manufacturing.

**Warning: Stresses above the max. values listed here may cause permanent damage to the device. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit. Exposure to conditions at or below absolute maximum rating but above the specified maximum operation conditions may affect device reliability and life time. Functionality of the device might not be given under these conditions.**

**Table 2: Thermal Resistance**

Parameter	Symbol	Value	Unit
Thermal Resistance - Junction - Solder (@25°C)	$R_{th,JS}$	21.3	°K/W
Thermal Resistance - Junction - Case-Top (@25°C)	$R_{th,Jc}$	105.9	°K/W

**Table 3: Recommended Operating Conditions**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply Voltage	$V_{CC}$	3.15	–	3.45	V	–
Enable Voltage OFF	$V_{EN,OFF}$	0	–	0.75	V	–
Enable Voltage ON	$V_{EN,ON}$	0.95	–	$V_{CC}$	V	–
Operating Temperature	$T_A$	-40	–	115	°C	Solder joint temperature

### 3 Electrical Characteristics

Table 4: Electrical Characteristics

Parameter	Symbol	Values <sup>1</sup>			Unit	Note / Test Condition <sup>2</sup>
		Min.	Typ.	Max.		
RF Frequency	$f_{RF}$	3300	–	4200	MHz	–
Current Consumption OFF	$I_{CC,OFF}$	–	1.7	–	mA	–
Current Consumption ON	$I_{CC,ON}$	–	152	210	mA	No RF input signal
Input Return Loss	$RL_{IN}$	–	15	–	dB	–
Output Return Loss	$RL_{OUT}$	–	15	–	dB	–
Gain	$G$	30.8	34.4	–	dB	–
Gain Flatness		–	–	0.5	dB	In any 100Mhz BW within RF band
Output P1dB	$OP_{1dB}$	24.5	27.8	–	dBm	–
Output IP3	$OIP_3$	–	37	–	dBm	$P_{IN1}=P_{IN2}=-30dBm, \Delta f=1MHz$
Adjacent Channel Leakage Ratio	$ACLR$	–	50	–	dBc	20MHz E-TM1.1 @Pout=15dBm
Common Mode Rejection Ratio	$CMRR$	24	–	–	dB	–
Noise Figure	$NF$	–	3.5	–	dB	–
ON/OFF Time	$T_{ON}, T_{OFF}$	–	2.5	–	$\mu s$	Gain within 0.1dB amplitude/1° phase of final value

<sup>1</sup>Min/Max values defined over process, voltage, temperature and frequency variations

<sup>2</sup>Test conditions (unless otherwise noted): T=25°C,  $V_{CC}=3.3V$ ,  $f_{RF}=3.6GHz$

## 4 Performance Variation

**Table 5: Gain Variation Contributions**

Parameter	Frequency Range			Unit
	3.4GHz-3.6GHz	3.3GHz-3.9GHz	3.3GHz-4.2GHz	
Typical	34.5	34.5	34.4	dB
Process Variation <sup>1</sup>	± 0.75	± 0.9	± 1.35	dB
Temperature Variation <sup>2</sup>	-0.018	-0.018	-0.019	dB/°C
Minimum	31.7	31.6	30.8	dB

<sup>1</sup>Process variation is based on simulation data ( $\pm 3\sigma$ )

<sup>2</sup>Temperature variation is based on measured data

**Table 6: OP1dB Variation Contributions**

Parameter	Frequency Range			Unit
	3.4GHz-3.6GHz	3.3GHz-3.9GHz	3.3GHz-4.2GHz	
Typical	27.4	27.8	27.8	dBm
Process Variation <sup>1</sup>	± 1.5	± 1.5	± 1.5	dB
Temperature Variation <sup>2</sup>	-0.008	-0.010	-0.010	dB/°C
Minimum	24.5	24.5	24.5	dBm

<sup>1</sup>Process variation is based on simulation data ( $\pm 3\sigma$ )

<sup>2</sup>Temperature variation is based on measured data

**Table 7: OIP3 Variation Contributions**

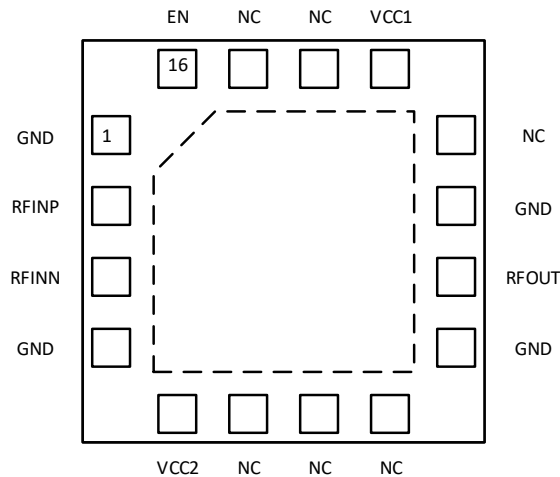
Parameter	Frequency Range			Unit
	3.4GHz-3.6GHz	3.3GHz-3.9GHz	3.3GHz-4.2GHz	
Typical	35.9	36.4	37	dBm
Process Variation <sup>1</sup>	± TBD	± TBD	± TBD	dB
Temperature Variation <sup>2</sup>	0.025	0.039	0.062	dB/°C
Minimum	TBD	TBD	TBD	dBm

<sup>1</sup>OIP3 simulation provides insufficient resolution. Process variations will be assessed from larger device volume.

<sup>2</sup>Temperature variation is based on measured data

## 5 Application Information

### Pin Configuration and Function



**Figure 2:** BGA7P320 Pin Configuration - Top View

**Table 8: Pin Definition and Function**

Pin No.	Name	Function
1, 4, 9, 11	GND	Ground
2	RFINP	RF Input +
3	RFINN	RF Input -
5	VCC2	2 <sup>nd</sup> stage DC voltage supply
6, 7, 8, 12, 14, 15	NC	Not connected internally. It can be either left floating or connected to ground.
10	RFOUT	RF Output
13	VCC1	1 <sup>st</sup> stage DC voltage supply
16	EN	Chip enable
Backside Paddle	GND	Ground connection

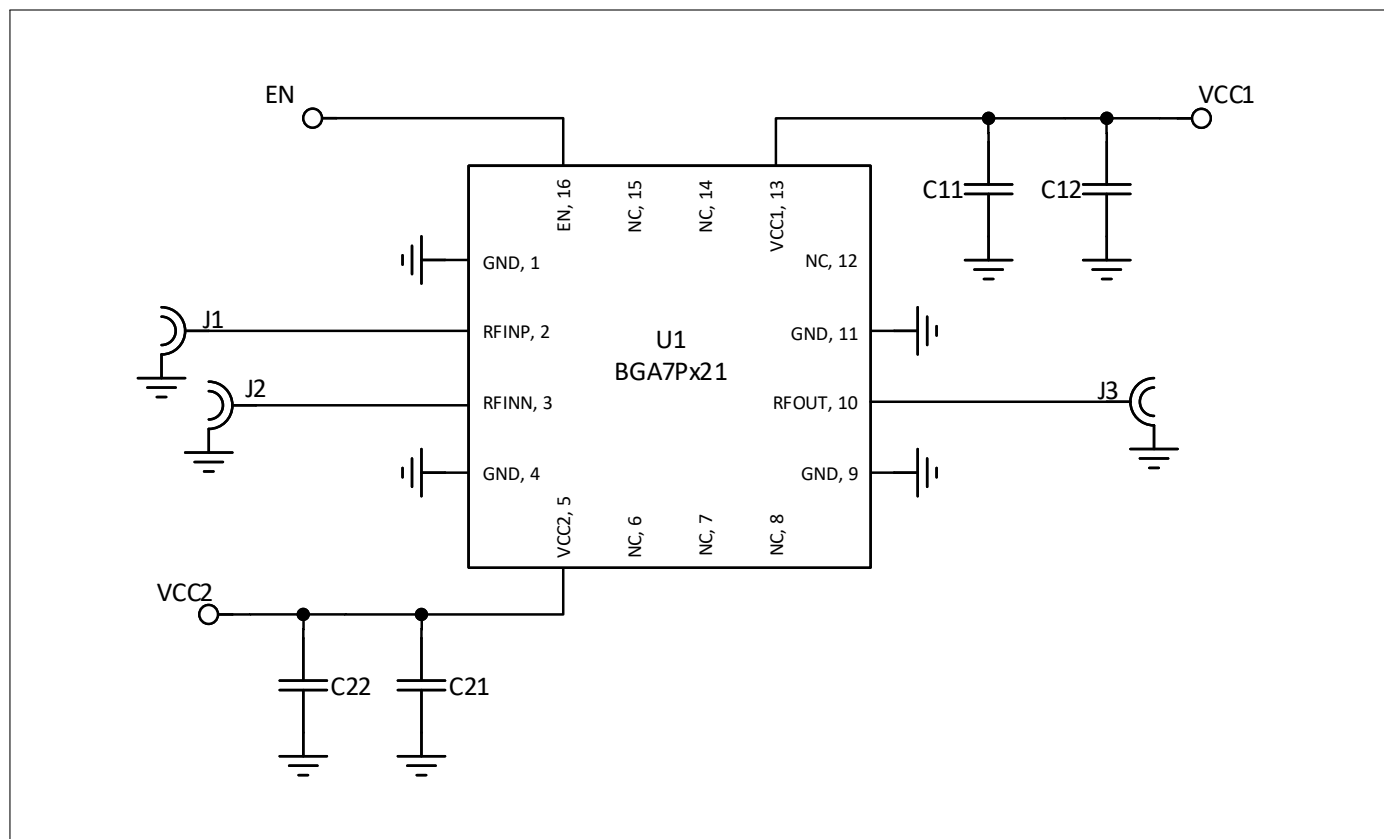
# BGA7P320

## Pre-Driver for Doherty Power Amplifier



### Application Information

### Application Board Configuration



**Figure 3:** BGA7P320 Application Schematic

**Table 9: Bill of Materials Table**

Name	Value	Description	Part Number	Manufacturer
C11, C21	10nF	Capacitor, X7R, 0402	–	Various
C12, C22	1uF	Capacitor, X7R, 0402	–	Various
J1, J2, J3	–	Connector, SMA	32K243-40ML5	Rosenberger
U1	–	Pre-driver, PG-TSNP-16-12	BGA7P320	Infineon

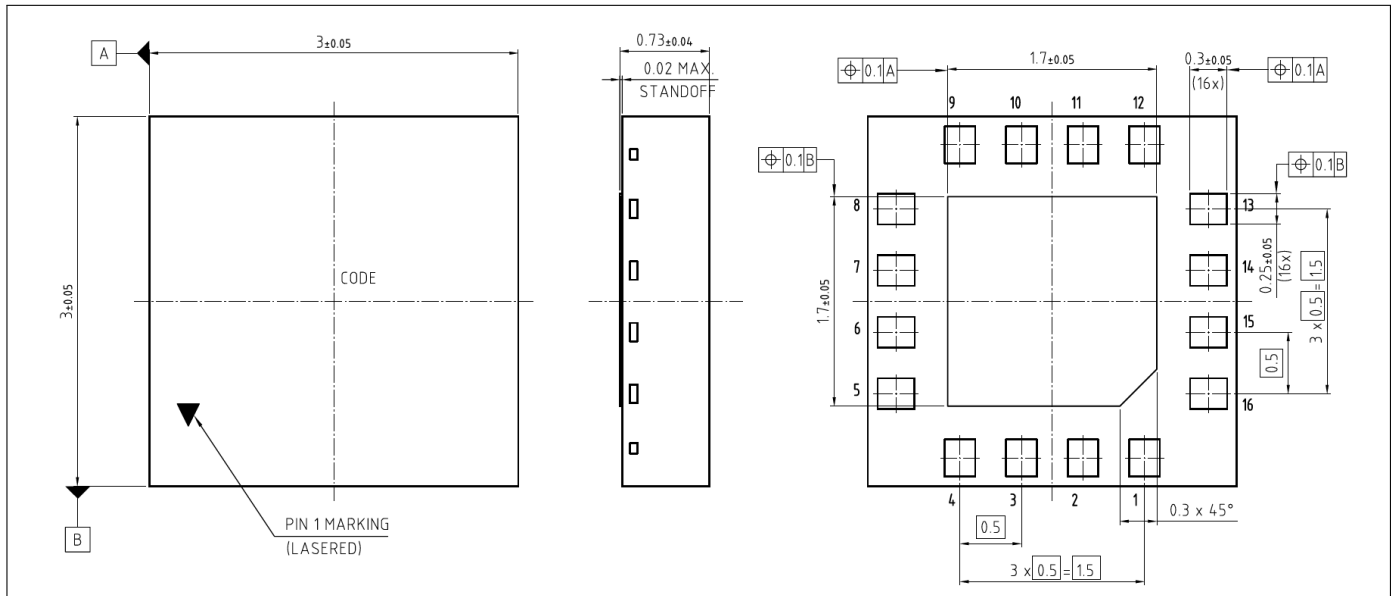


# BGA7P320

## Pre-Driver for Doherty Power Amplifier

### Package Information

## 6 Package Information



**Figure 4:** PG-TSNP-16-12 Package Outline (3.0mm x 3.0mm x 0.73mm)

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**Revision History**

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**1.0**

<b>Page or Item</b>	<b>Subjects (major changes since previous revision)</b>
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**Revision 1.1, 2021-06-22**

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**Revision History**

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pag. 4	Updated ACLR value and test condition

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**Edition 2021-06-22**  
**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**

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